

●Electrical and optical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Light current	Ic	2.0	—	—	mA	V _{CE} =5V, E=500Lx
Dark current	I _{CEO}	—	—	0.5	μA	V _{CE} =10V(Black box)
Peak sensitivity wavelength	λ _P	—	800	—	nm	—
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	0.4	V	I _c =1mA, E=500Lx
Half-angle	θ _{1/2}	—	±36	—	deg	—
Response time	tr · tf	—	10	—	μs	V _{CC} =5V, I _c =1mA, R _L =100Ω

●Electrical and optical characteristic curves

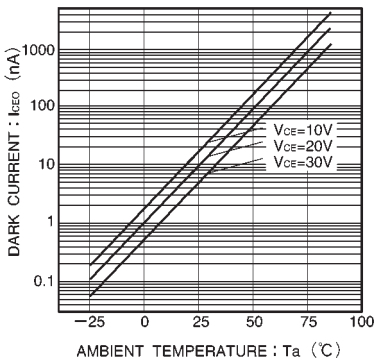


Fig.1 Dark current vs. ambient temperature

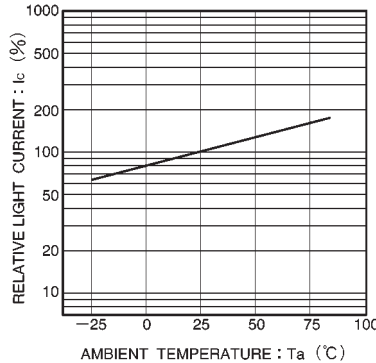


Fig.2 Relative output vs. ambient temperature

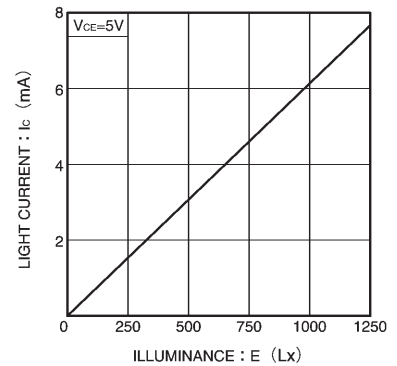


Fig.3 Light current vs. irradiance

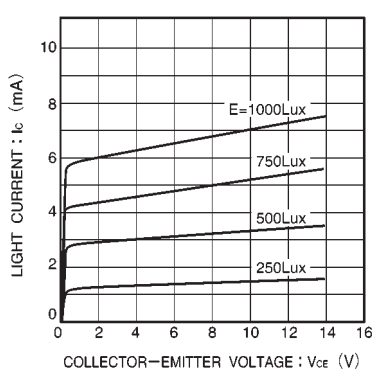


Fig.4 Output characteristics

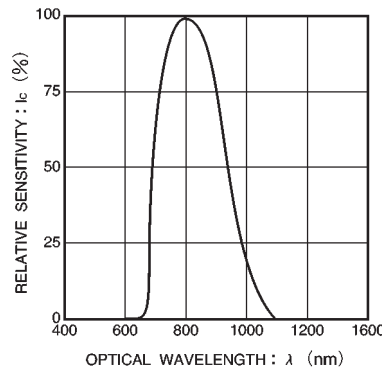


Fig.5 Spectral sensitivity

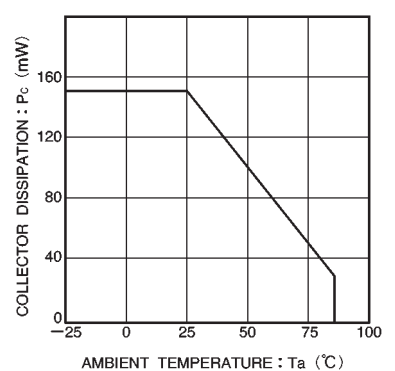


Fig.6 Collector dissipation vs. ambient temperature

Phototransistors

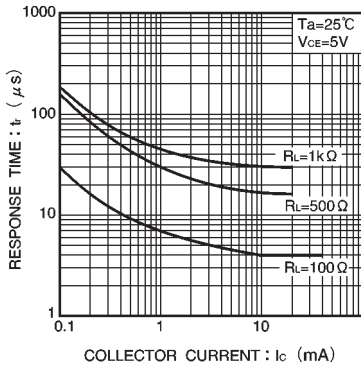


Fig.7 Response time vs. collector current

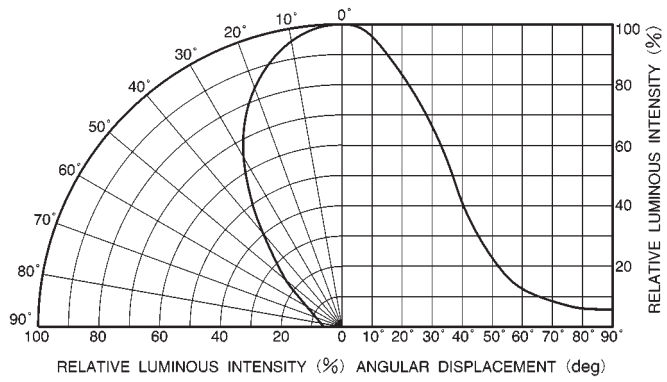


Fig.8 Directional pattern